

IR2159

DIMMING BALLAST CONTROLLER IC

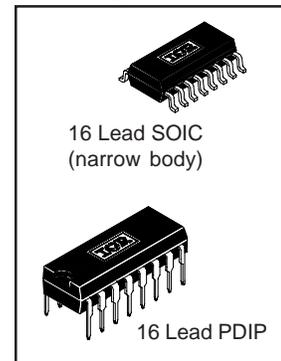
Features

- Ballast control and half-bridge driver in one IC
- Transformerless lamp power sensing
- Closed-loop lamp power control
- Closed loop preheat and ignition current control
- Programmable preheat time
- Programmable preheat current
- Programmable ignition-to-dim time
- 0.5 to 5VDC or 0 to 5VDC dimming control input
- Min and max lamp power adjustments
- Programmable deadtime
- Internal current sense blanking
- Full lamp fault protection
- Automatic restart
- Micro-power startup
- Zener clamped Vcc
- Over-temperature protection
- 16-pin DIP and SOIC package types

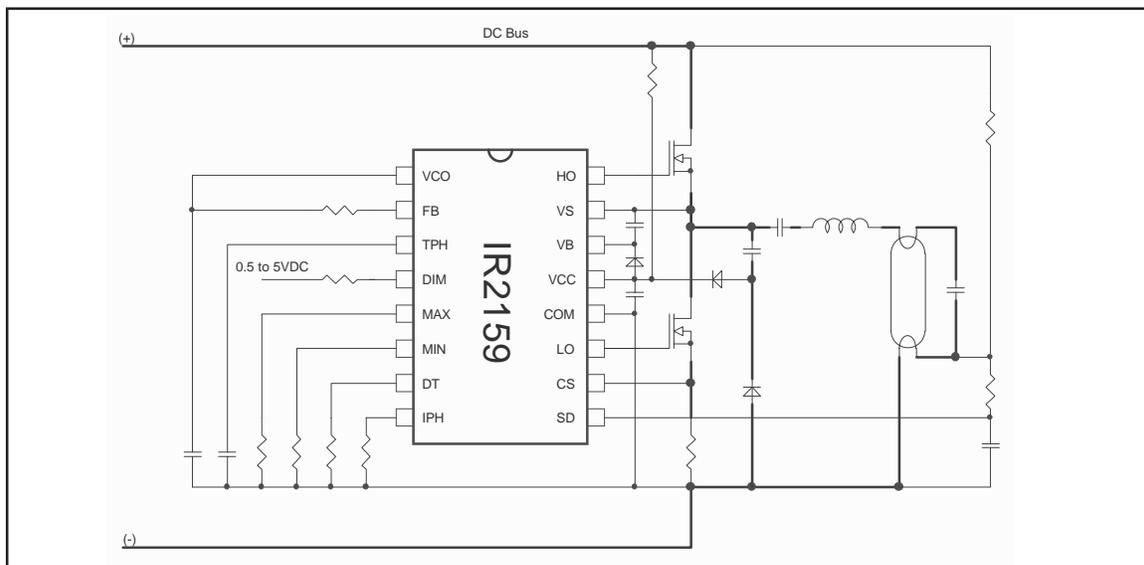
Description

The IR2159 is a complete dimming ballast controller and 600V half-bridge driver all in one IC. The architecture includes phase control for transformerless lamp power sensing and regulation which minimizes changes needed to adapt non-dimming ballast for dimming. Externally programmable features such as preheat time and current, ignition-to-dim time, and a complete dimming interface with minimum and maximum settings provide a high degree of flexibility for the ballast design engineer. Protection from failure of a lamp to strike, filament failures, thermal overload, or lamp failure during normal operation, as well as an automatic restart function, have been included in a design. The heart of this control IC is a voltage controlled oscillator with externally programmable deadtime. The IR2159 is available in both 16 pin DIP and 16 pin narrow body SOIC packages.

Packages



Typical Connection



Absolute Maximum Ratings

Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM, all currents are defined positive into any lead. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
V _B	High side floating supply voltage	-0.3	625	V
V _S	High side floating supply offset voltage	V _B - 25	V _B + 25	
V _{HO}	High side floating output voltage	V _S - 0.3	V _B + 0.3	
V _{LO}	Low side output voltage	-0.3	V _{CC} + 0.3	
I _{OMAX}	Maximum allowable output current (either output) due to external power transistor miller effect	-500	500	mA
V _{VCO}	Voltage controlled oscillator input voltage	-0.3	5.0	V
I _{TPH}	TPH current	-5	5	mA
V _{IPH}	IPH voltage	0.3	5.5	V
V _{DIM}	Dimming control pin input voltage	0.3	5.5	
V _{MAX}	Maximum lamp power setting pin input voltage	0.3	5.5	
V _{MIN}	Minimum lamp power setting pin input voltage	-0.3	5.5	
V _{CS}	Current sense input voltage	-0.3	5.5	
I _{SD}	Shutdown pin current	-5	5	mA
I _{CC}	Supply current (note 1)	—	25	
dV/dt	Allowable offset voltage slew rate	-50	50	V/ns
P _D	Package power dissipation @ T _A ≤ +25°C	—	TBD	W
R _{thJA}	Thermal resistance, junction to ambient	—	TBD	°C/W
T _J	Junction temperature	-55	150	°C
T _S	Storage temperature	-55	150	
T _L	Lead temperature (soldering, 10 seconds)	—	300	

Note 1: This IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Please note that this supply pin should not be driven by a DC, low impedance power source greater than the diode clamp voltage (V_{CLAMP}) as specified in the Electrical Characteristics section.

Recommended Operating Conditions

For proper operation the device should be used within the recommended conditions.

Symbol	Definition	Min.	Max.	Units
V _{BS}	High side floating supply voltage	V _{CC} - 0.7	V _{CLAMP}	V
V _S	Steady state high side floating supply offset voltage	-1	600	
V _{CC}	Supply voltage	V _{CCUV+}	V _{CLAMP}	mA
I _{CC}	Supply current	note 2	10	
V _{VCO}	V _{CO} pin voltage	1	5	V
V _{DIM}	Dim pin voltage	0	5	
V _{MAX}	MAX pin current (note 3)	-750	0	μA
V _{MIN}	MIN pin current	1	3	V
R _{DT}	Deadtime resistance	20.0	40.0	kΩ
I _{SD}	Shutdown lead current	-1	1	mA
I _{CS}	Current sense lead current	-1	1	
T _J	Junction temperature	-40	125	°C

Electrical Characteristics

V_{CC} = V_{BS} = V_{BIAS} = 15V +/- 0.25V, V_{CS} = 0.5V, V_{SD} = 0.0V, R_{DT} = 40k, C_{VCO} = 10 nF, V_{DIM} = 0.0V, R_{MAX} = 33k, R_{MIN} = 56k, V_{TPH} = 0.0V, C_L = 1000pF, T_A = 25°C unless otherwise specified.

Supply Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{CCUV+}	V _{CC} supply undervoltage positive going threshold	—	12.5	—	V	
V _{CC} HYS	V _{CC} supply undervoltage lockout hysteresis	—	1.6	—		
I _{QCCUV}	UVLO mode quiescent current	—	150	—	μA	V _{CC} < V _{CCUV-} SD=5V, CS=2V, or T _j > T _{SD}
I _{QCCFLT}	Fault-mode quiescent current	—	200	—		
I _{QCC}	Quiescent V _{CC} supply current	—	TBD	—	mA	
I _{QCC50K}	V _{CC} supply current, f= 50kHz	—	4.5	—		
V _{CLAMP}	V _{CC} zener clamp voltage	—	15.6	—	V	I _{CC} = 10mA

Note 2: Enough current should be supplied into the V_{CC} lead to keep the internal 15.6V zener clamp diode on this lead regulating its voltage.

Note 3: The MAX lead is a voltage-controlled current source. For optimum dim interface current mirror performance, this current should be kept between 0 and 750μA.

Electrical Characteristics (cont.)

$V_{CC} = V_{BS} = V_{BIAS} = 15V \pm 0.25V$, $V_{CS} = 0.5V$, $V_{SD} = 0.0V$, $R_{DT} = 40k$, $C_{VCO} = 10 \text{ nF}$, $V_{DIM} = 0.0V$, $R_{MAX} = 33k$, $R_{MIN} = 56k$, $V_{TPH} = 0.0V$, $C_L = 1000pF$, $T_A = 25^\circ\text{C}$ unless otherwise specified.

Floating Supply Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
I_{QBS0}	Quiescent V_{BS} supply current	—	0	—	μA	$V_{HO} = V_S$
I_{QBS1}	Quiescent V_{BS} supply current	—	30	—		$V_{HO} = V_B$
V_{BSMIN}	Minimum required V_{BS} voltage for proper HO functionality	—	4	5	V	
I_{LK}	Offset supply leakage current	—	—	50	μA	$V_B = V_S = 600V$
Oscillator I/O Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
f_{VCO}	Voltage controlled oscillator frequency	—	20	—	kHz	$V_{VCO} = 1V$
		—	100	—		$V_{VCO} = 5V$
df/dV_{CC}	Oscillator frequency voltage stability	—	TBD	—	%	$V_{VCO} = \text{TBD}$ $V_{CCUV+} < V_{CC} < 15V$
df/dT	Oscillator frequency temperature stability	—	TBD	—	%	$V_{VCO} = \text{TBD}$ $-40^\circ\text{C} < T_j < 125^\circ\text{C}$
d	Gate drive outputs duty cycle	—	50	—	%	$V_{VCO} = \text{TBD}$
V_{VCOFLT}	Fault-mode VCO pin voltage (UVLO, shutdown, over-current/temp.)	—	5		V	
I_{VCOPH}	Preheat mode VCO pin discharge current		1.0		μA	$V_{TPH} < 4V$
I_{VCOIG}	Ignition mode VCO pin discharge current		1.0		μA	$4V < V_{TPH} < 5V$
I_{VCOPK}	Peak current control VCO pin charging current		60.0		μA	$V_{CS} > V_{CSTH}$
I_{VCODIM}	Dim mode VCO pin discharge current		16.0		μA	
td_{LO}	LO output deadtime	—	2.0	—	μs	$R_{DT} = 40K$
td_{HO}	HO output deadtime	—	2.0	—		
dtd/dV_{CC}	Deadtime voltage stability	—	TBD	—	%	$V_{CCUV+} < V_{CC} < 15V$
dtd/dT	Deadtime temperature stability	—	TBD	—	%	$-40^\circ\text{C} < T_j < 125^\circ\text{C}$
Gate Driver Output Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V_{OL}	Low-Level Output Voltage	—	—	100	mV	
V_{OH}	High-Level Output Voltage	—	—	100	mV	$V_{BIAS} - V_O$
t_r	Turn-On Rise Time	—	—	150	ns	
t_f	Turn-Off Fall Time	—	—	100	ns	

Electrical Characteristics (cont.)

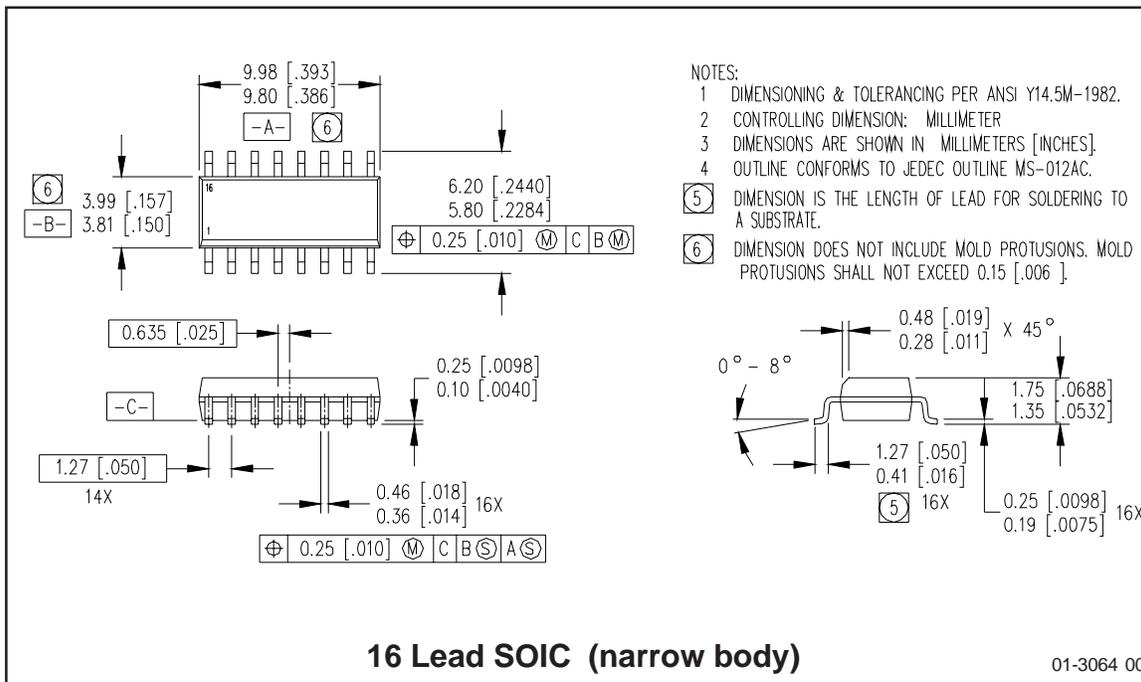
$V_{CC} = V_{BS} = V_{BIAS} = 15V \pm 0.25V$, $V_{CS} = 0.5V$, $V_{SD} = 0.0V$, $R_{DT} = 40k$, $C_{VCO} = 10 \text{ nF}$, $V_{DIM} = 0.0V$, $R_{MAX} = 33k$, $R_{MIN} = 56k$, $V_{TPH} = 0.0V$, $C_L = 1000pF$, $T_A = 25^\circ C$ unless otherwise specified.

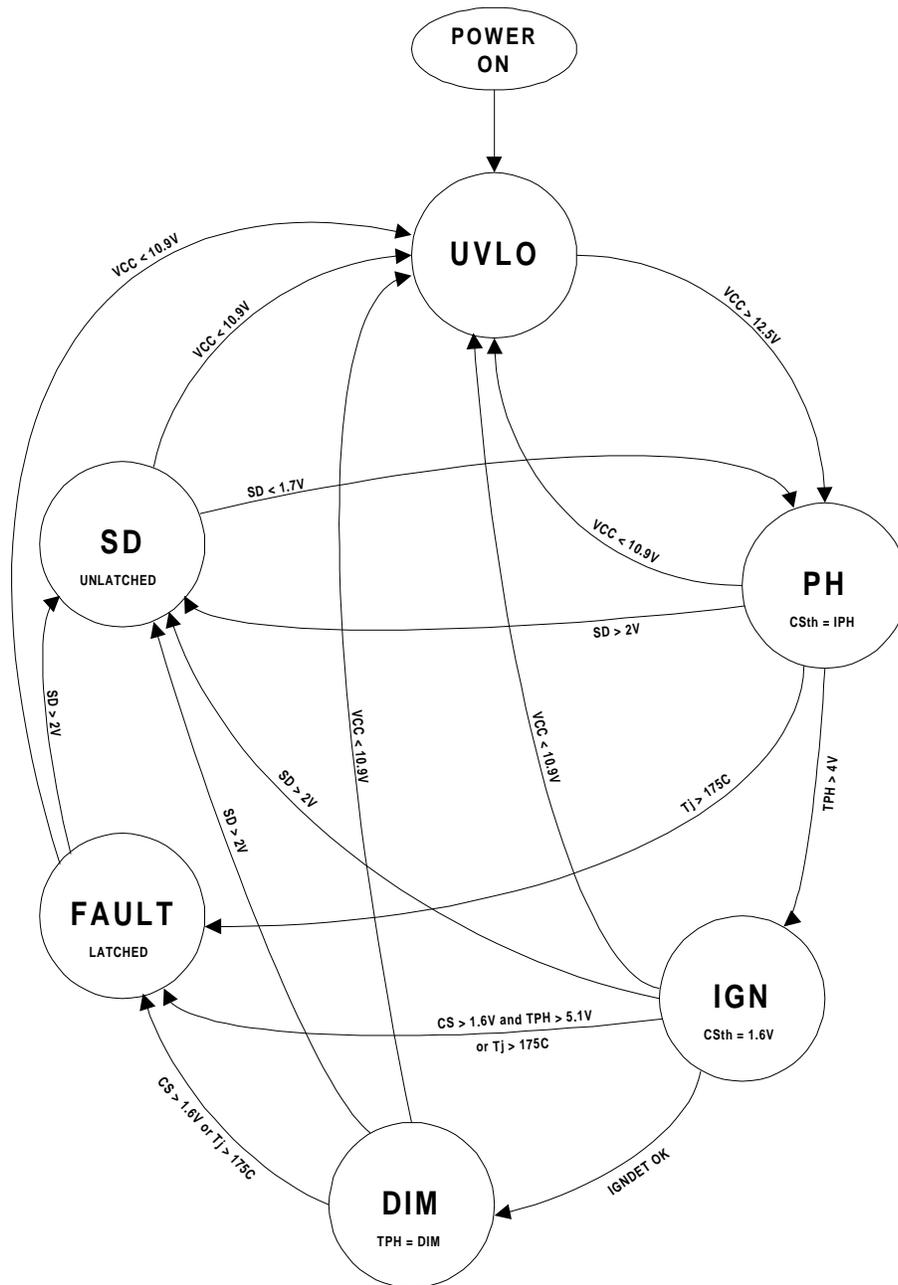
Preheat Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
I _{TPH}	TPH pin charging current	---	1.0	---	μA	I _{TPH} = 0.04/RDT
V _{TPHIGN}	TPH pin ignition mode threshold voltage		4.0		V	
V _{TPHCLMP}	TPH pin clamp voltage		7.6		V	
I _{IPH}	IPH pin DC source current		25.0		μA	I _{IPH} = 1/RDT
V _{CSTH}	Peak preheat current regulation threshold (Programmable)	0.7		V		V _{CSTH} = (I _{IPH}) x (R _{IPH})
Ignition Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{CSTH}	Peak ignition current regulation threshold	—	1.6	—	V	4V < V _{TPH} < 5V
Protection Characteristics						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{SDTH+}	Rising shutdown pin threshold voltage	—	3.0	—	V	
V _{SDHYS}	SD threshold hysteresis	—	150	—	mV	
V _{SDCLAMP}	SD pin clamp voltage	—	7.6	—		
V _{CSTH}	Peak over-current latch threshold voltage	—	1.6	—	V	
T _{SD*}	Thermal shutdown junction temperature	—	175	—	°C	
Phase Control						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{CSTHZX}	Zero-crossing threshold voltage	—	0.0	—	V	
R _{DSFB}	FB pin on resistance (open drain)	—	125	—	Ω	
Dim Interface						
Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
V _{DIMOFF}	DIM pin offset voltage	—	0.5	—		
V _{DIM}	DIM input voltage range	0.0	—	5.0		
V _{MIN}	DIM reference voltage range (MIN pin)	1.0	—	3.0		

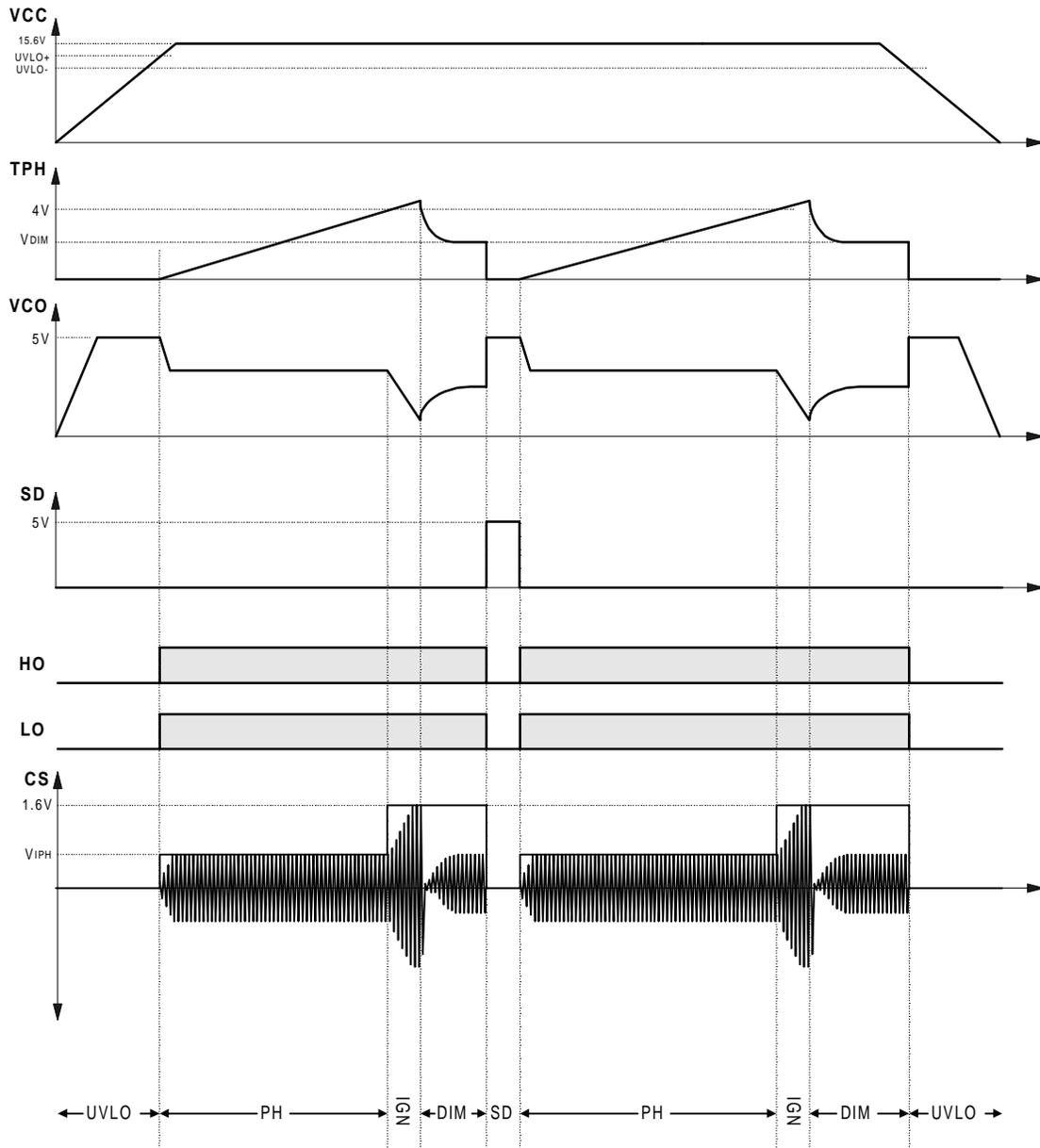
* When the IC senses an overtemperature condition ($T_j > 125^\circ C$), the chip is latched off. In order to reset this Latch, the supply to the IC must be cycled below the falling undervoltage lockout threshold, V_{CC-} , or the SD pin must be cycled.

Lead Assignments & Definitions

Lead #	Symbol	Description	Pin Assignments	
1	VCO	Voltage controlled oscillator input	1	HO
2	FB	Feedback gain	2	VS
3	TPH	Preheat timing input	3	VB
4	DIM	0.5 to 5VDC dimming control input	4	VCC
5	MAX	Maximum lamp power setting	5	COM
6	MIN	Minimum lamp power setting	6	LO
7	DT	Deadtime programming	7	CS
8	IPH	Peak preheat current reference	8	SD
9	SD	Shutdown input	9	
10	CS	Current sensing input	10	
11	LO	Low-side gate driver output	11	
12	COM	IC Power & signal ground	12	
13	VCC	Logic & low-side gate driver supply	13	
14	VB	High-side gate driver floating supply	14	
15	VS	High voltage floating return	15	
16	HO	High-side gate driver output	16	



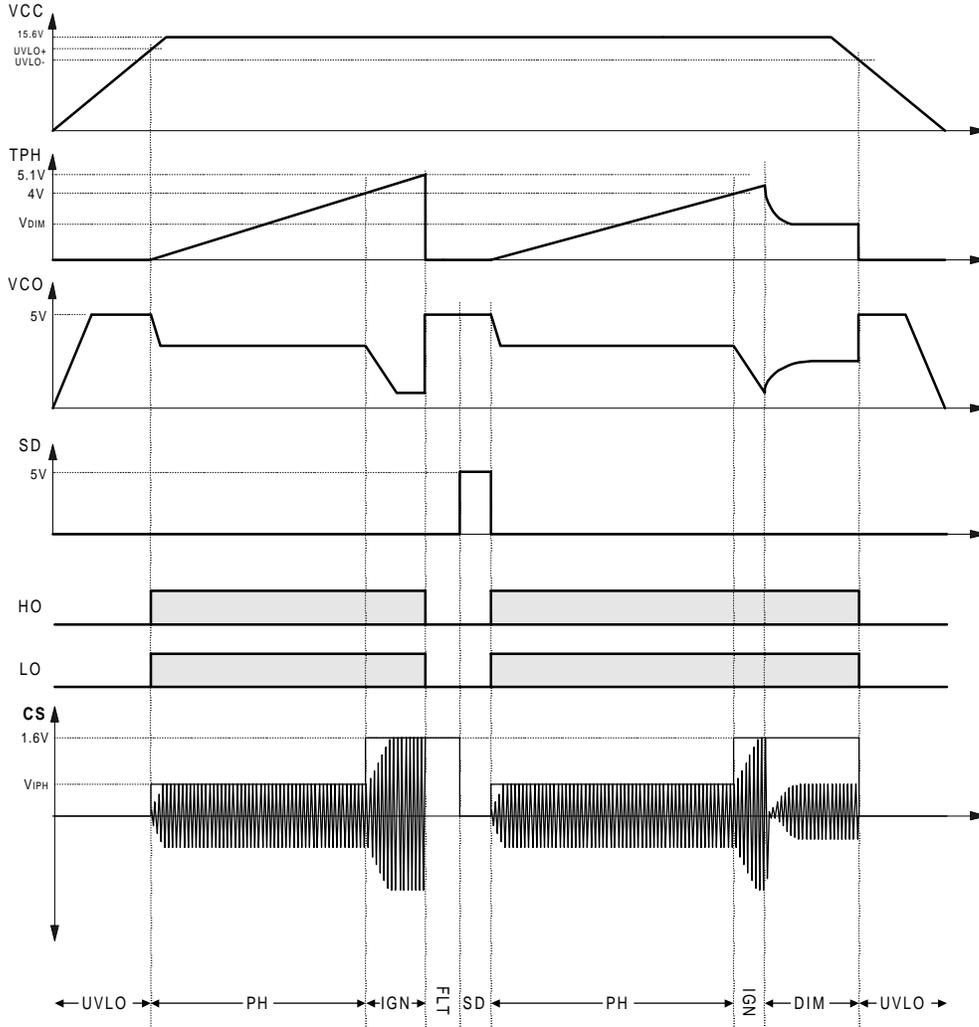




IR2159

ADVANCED INFORMATION

International
IR Rectifier



International
IR Rectifier

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245 Tel: (310) 322 3331

IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020

IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T 3Z2 Tel: (905) 453-2200

IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590

IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111

IR FAR EAST: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo, Japan 171 Tel: 81 3 3983 0086

IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: 65 838 4630

IR TAIWAN: 16 Fl. Suite D..207, Sec.2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936

<http://www.irf.com/>

Data and specifications subject to change without notice. 3/1/99